

## **REVOCATION AND POWER OF ATTORNEY**

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

SIR:

EKC Technology, Inc., owner of the entire right, title and interest in, to and under the inventions described and claimed in the patent applications identified in the attached Schedule A, hereby revokes all previous powers of attorney and appoints Morgan, Lewis & Bockius LLP, customer no. 24341, and each of them, its attorneys, to prosecute each of these patent applications, and to transact all business in the Patent and Trademark Office connected therewith.

Please direct all future correspondence to Customer Number 24341, Morgan, Lewis & Bockius LLP, located at 3300 Hillview Avenue, Palo Alto, California 94304, and direct all telephone calls to Morgan, Lewis & Bockius LLP at (650) 493-4935.

Assignee:

EKC Technology, Inc.

Date:

7 feb 2004

Signature:

Michael A. Fury

Typed Name: Position/Title:

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	Schedule A					
App #12.5	sTitle s	- ≟Inventor(s) √	Filing Date	New Attorney & Docket No. 2	Former Attorney	
	Compositions for Cleaning Organic					
	and Plasma Etched Residues for					
09/903,064	Semiconductor Devices	Small, et al.	07/10/2001	60937-091-US	8317-091-999	
	Method of and Apparatus for					
09/874,330	Substrate Pre-Treatment	Maloney, et al.	06/06/2001	60937-111-US	8317-111-999	
00/005 070	Chemical Mechanical Polishing	0	44/00/0004	00007 444 440		
09/985,870	Compositions	Small, et al.	11/06/2001	60937-114-US	8317-114-999	
	Oxalic Acid as a Semiaqueous Cleaning Product for Copper and					
10/421,706	Dielectrics	Locatel	04/24/2003	60027 116 116	9247 440 000	
10/421,700	Sulfoxide Pyrolid(in)one Alkanolamine	Lee, et al.	04/24/2003	60937-116-US	8317-116-999	
10/193,185	Cleaner Composition	Zhou, et al.	07/12/2002	60937-118-US	8317-118-999	
10/100,100	Clourer Composition	Zilou, et al.	0171212002	00937-110-03	0317-110-999	
	Method for the Deposition of Materials					
09/876,944	from Mesomorphous Films	Vasquez, et al.	06/08/2001	60937-120-US	8317-120-999	
· · · · · · · · · · · · · · · · · · ·	Post Etch Cleaning Composition for				0011 120 000	
10/007,134	Dual Damascene System	Payne, et al.	12/04/2001	60937-123-US	8317-123-999	
	Photolytic Conversion Process to					
10/263,701	Form Patterned Amorphous Film	Bravo-Vasquez, et al.	10/04/2002	60937-126-US	8317-126-999	
	Cleaning Solutions Including					
	Nucleophilic Amine Compound					
	Having Reduction and Oxidation					
09/988,545	Potential	Lee, et al.	11/20/2001	60937-127-US	8317-127-999	
	Method and Compositions for					
10/060,109	Chemically Treating A Substrate	Datal at at	04/00/0000	00007.400.110	2017 100 000	
10/000,109	Using Foam Technology Cleaning Solution Including	Patel, et al.	01/28/2002	60937-129-US	8317-129-999	
	Nucleophilic Amine Compound					
1	Having Reduction and Oxidation					
10/135,695	Potential	Lee, et al.	05/01/2002	60937-135-US	8317-135-999	
10/448,127	Fluoride Layer and Removing Same	Melvin K. Carter	05/30/2003	60937-137-US	8317-137-999	
	Process for the Use of Bis-Choline				0011 101 000	
	and Tris-Choline in the Cleaning of					
	Quartz-Coated Polysilicon and Other					
10/689,657	Materials	Charm, et al.	10/22/2003	60937-139-US	8317-139-999	
	Cleaning Compositions Containing					
	Hydroxylamine Derivatives and					
	Process Using Same for Residue					
10/689,620	Removal	Zhou, et al.	10/22/2003	60937-140-US	8317-140-999	
			<del>.</del>			
40/000 515	Composition for Exfoliation Agent to					
10/689,616	be Used to Remove Resist Residues	Melvin K. Carter	10/22/2003	60937-141-US	8317-141-999	
	Reducing Oxide Loss When Using	!				
ŀ	Fluoride Chemistries to Remove Post- Etch Residues in Semiconductor					
60/467,131	Processing	Leo et al	05/02/2002	60037 142 DD	9317 142 000	
30/707,131	i rocessing	Lee, et al.	05/02/2003	60937-142-PR	8317-142-888	

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Ápp.#	Title	≨a√Inventor(s)	Filing Daté	Mew:Attorney	Former Attorney  Docket No.
	Method for Depositing Patterned				
10/630,301	Films of Materials	Hill, et al.	07/30/2003	60937-143-US	8317-143-999
	Methods for the Deposition of Silver				
	and Silver Oxide Films and Patterned				
10/716,838	Films	Ruan, et al.	11/18/2003	60937-147-US	8317-147-999
10/100 070	Semiconductor Process Residue		00/00/000		2017 110 222
10/162,679	Removal Composition and Process System and Method for Cleaning	Lee, et al.	06/06/2002	60937-149-US	8317-149-999
	Workpieces Using Supercritical				
60/469,826	Carbon Dioxide	Fury, et al.	05/13/2003	60937-150-PR	8317-150-888
00/409,020	Carbon bloxide	r dry, et al.	03/13/2003	00937-130-FIX	0317-130-000
	Abrasive-Free Chemical Mechanical				
	Polishing Composition and Polishing				
10/689,043	Process Containing Same	Yao, et al.	10/21/2003	60937-151-US	8317-151-999
		·			
10/689,042	Wet Etch of Titanium-Tungsten Film	Patel, et al.	10/21/2003	60937-152-US	8317-152-999
	Method of Depositing Nanostructured				
10/261,197	Films with Embedded Nanopores	Svendsen, et al.	09/30/2002	60937-153-US	8317-153-999
40,000,000	Hydrothermal Treatment of				
10/280,270	Nanostructured Films	Mukherjee, et al.	10/23/2002	60937-167-US	8317-167-999
10/257,469	Inhibition of Titanium Corrosion	Daviot, et al.	10/11/2002	60937-168-US	8317-168-999
10/401,405	Chemical Mechanical Polishing Composition and Process	Small, et al.	03/27/2003	60937-171-US	8317-171-999
10/401,403	Aqueous Phosphoric Acid	Sinali, et al.	03/2/12003	00937-171-03	0317-171-999
	Compositions for Cleaning				¢.
10/688,900	Semiconductor Devices	Daviot, et al.	10/21/2003	60937-172-US	8317-172-999
	Load Lock System for Supercritical				
10/465,906	Fluid Cleaning	Fury, et al.	06/18/2003	60937-175-US	8317-175-999
	Automated Dense Phase Fluid				
10/465,905	Cleaning System	Fury, et al.	06/18/2003	60937-176-US	8317-176-999
	Residue Removers for				
004477 155	Electrohydrodynamic Cleaning of				
60/455,439	Semiconductors	Robert J. Small	03/18/2003	60937-178-PR	8317-178-888
	Free Radical-Forming Activator				
10/06:	Attached to Solid and Used to				
10/361,822	Enhance CMP Formulations	Scott, et al.	02/11/2003	60937-179-US	8317-179-999
10/277 522	Titanium Carboxylate Films for Use in	1100 -4 -4	00/00/0000	00007 400 440	0047 400 000
10/377,533	Semiconductor Processing  Method of Making Barrier Layers	Hill, et al.	02/26/2003	60937-182-US	8317-182-999
10/422,860	Remover Formulation Containing	Maloney, et al.	05/20/2003	60937-183-US	8317-183-999
3	Fluoride for Use During				
60/463,739	Semiconductor Manufacturing	Hirasawa, et al.	04/18/2003	60937-185-PR	8317-185-888
1230,00	Cleaning Composition for Removing	. maama, or an		3000. 1001.10	3011 100 000
	Resists and Manufacturing Method of				
60/464,125	Semiconductor Devices	Hirasawa, et al.	04/21/2003	60937-186-PR	8317-186-888
	Deposition of Permanent Polymer				
10/422,212	Structures for OLED Fabrication	Roman, et al.	04/23/2003	60937-187-US	8317-187-999

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Apps# &	. Title		Filing Date	New Attorney Docket No.	Former Attorney Docket No.
	Seimconductor Process Residue				
10/442,858	Removal Composition and Process	Wai Mun Lee	05/20/2003	60937-189-US	8317-189-999
	Cleaning Compositions and Method of				
10/630,300	Use Thereof	Wai Mun Lee	07/30/2003	60937-194-US	8317-194-999
	Compositions and Methods for				,
	Rapidly Removing Overfilled				
60/518,337	Substrates	Chelle, et al.	11/10/2003	60937-200-PR	8317-200-888
	CMP Method for Copper, Tungsten,				
-	Titanium, Polysilicon, and Other				
40/600 633	Substrates Using Organosulfonic Acids as Oxidizers	Cortor at al	10/22/2002	60027 202 116	9247 202 000
10/690,623	PeriodicAcid Compositions for	Carter, et al.	10/23/2003	60937-202-US	8317-202-999
	Polishing Nobel Metal/High K				
60/494,954	Substrates	Robert J. Small	08/14/2003	60937-203-PR	8317-203-888
00/434,334	Cerium Oxide Abrasives for Chemical	Nobell J. Siliali	00/14/2003	00937-203-FR	0317-203-000
60/509,920	Mechanical Polishing	Robert J. Small	10/10/2003	60937-204-PR	8317-204-888
00/000,020	Woodanioa i Gilorinig	Trobott of Official	10/10/2000	00001 204111	0011-20 000
	Chemical Mechanical Polishing				
	Slurries and Cleaners Containing				
60/516,736	Salicyclic Acid as a Corrosion Inhibitor	Carter, et al.	11/04/2003	60937-206-PR	8317-206-888
	Periodic Acid Compositions for				
60/494,955	Polishing Ruthenium Substrates	Robert J. Small	08/14/2003	60937-207-PR	8317-207-888
	Chemical Mechanical Polishing				
10/683,730	Compositions and Process	Small, et al.	10/10/2003	60937-211-US	8317-211-999
	Alumia Abrasive for Chemical				
60/514,020	Mechanical Polishing	Philippe H. Chelle	10/27/1999	60937-213-PR	8317-213-888
	Chemical Mechanical Polishing				
	Slurries and Cleaners Containing				
60/502,951	Salicyclic Acid as a Corrosion Inhibitor	Tamilmani, et al.	09/16/2003	60937-214-PR	8317-214-888
	Compositions for Chemical				
40/005 447	Mechanical Planarization of Tantalum	0	00/00/0000	00007 045 110	0247 045 000
10/665,417	and Tantalum Nitride Alumina Abrasive for Chemical	Small, et al.	09/22/2003	60937-215-US	8317-215-999
60/526,107	Mechanical Polishing	Chelle, et al.	12/02/2003	60937-216-PR	8317-216-888
00/320,107	Particulate or Particle-Bound	Offelle, et al.	12/02/2003	00937-210-FK	0317-210-000
60/509,922	Chelating Agents	Small, et al.	10/10/2003	60937-217-PR	8317-217-888
00/000,022	Particulate or Particle-Bound	Oman, or an	10/10/2000	00001 217 110	0017 217 000
10/690,626	l .	Small, et al.	10/23/2003	60937-217-US	8317-217-999
	Chemical Mechanical Polishing of STI				
	Features on Semiconductors: Water				
60/533,054		Yu, et al.	12/30/2003	60937-223-PR	8317-223-888
	Removal of Post Etch Residues and				
	Copper Contamination From Low-K				
	Dielectrics Using Superciritcal CO2				
60/511,949	with Diketone Additives	Jerome Daviot	10/14/2003	60937-225-PR	8317-225-888
40/004 055	Method and Apparatus for Substrate		10/06/2222		0047 000 000
10/694,999	Pre-Treatment	Lee, et al.	10/29/2003	60937-226-US	8317-226-999

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	Method of Chemically Mechanically				
60/515,450	Polishing Substrates	Brandon S. Scott	10/30/2003	60937-228-PR	8317-228-888

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